

Solid State Physics Exercise Sheet 10

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Exercise 1 Electron / hole density and Hall effect in GaAs In the lecture, we derived for the electron density $n = 2 \left(\frac{m_e k_B T}{2\pi\hbar^2}\right)^{3/2} \exp[(\mu - E_c)/k_B T]$ and a similar formula for the hole density p.

- (a) Use the effective mass and the band gap (see table values of the lecture slides) to estimate n and p (for light holes).
- (b) Calculate the Hall coefficient if only holes or electrons contribute.

Exercise 2 Hall effect: Multiband scenario

In the lecture we derived single-band expressions for the resistivity $\rho = m/ne^2\tau$ and the Hall coefficient $R_{\rm H} = -1/ne$. It is convenient to write the relation between the current density **j** and the electric field **E** as $\mathbf{E} = \rho \mathbf{j}$ where:

$$\boldsymbol{\rho} = \begin{pmatrix} \rho & -R_{\rm H}B\\ R_{\rm H}B & \rho \end{pmatrix} \tag{1}$$

(a) Let us consider a metal where more than one band crosses the Fermi level. When applying an electric field **E**, the current \mathbf{j}_n on the n^{th} band is: $\mathbf{j}_n = \boldsymbol{\rho}_n^{-1} \mathbf{E}$ where

$$\boldsymbol{\rho}_n = \begin{pmatrix} \rho_n & -R_{\mathrm{H},n}B\\ R_{\mathrm{H},n}B & \rho_n \end{pmatrix}.$$
(2)

Show that the total induced current **j** is given by $\mathbf{E} = \boldsymbol{\rho} \mathbf{j}$ where $\boldsymbol{\rho} = (\sum \boldsymbol{\rho}_n^{-1})^{-1}$.

(b) If only two bands are crossing the Fermi level, show that:

$$R_{\rm H} = \frac{R_{\rm H,1}\rho_2^2 + R_{\rm H,2}\rho_1^2 + R_{\rm H,1}R_{\rm H,2}(R_{\rm H,1} + R_{\rm H,2})B^2}{(\rho_1 + \rho_2)^2 + (R_{\rm H,1} + R_{\rm H,2})^2B^2}$$
(3)

$$\rho = \frac{\rho_1 \rho_2 (\rho_1 + \rho_2) + (\rho_1 R_{\mathrm{H},2}^2 + \rho_2 R_{\mathrm{H},1}^2) B^2}{(\rho_1 + \rho_2)^2 + (R_{\mathrm{H},1} + R_{\mathrm{H},2})^2 B^2} \tag{4}$$

Hint: It is allowed to use Mathematica. If you do so, print out the code and the output.

- (c) Magnetic field dependence of resistivity is called magneto-resistance. If the two-band system has both electron-like and hole-like carries so that $|R_{\rm H,1}| \approx |R_{\rm H,2}|$, what is the field dependence of ρ ?
- (d) The mobility can be expressed as $\mu = e\tau/m$. Use the low-field limits of equations 3 and 4 to derive the following two expressions:

$$\sigma = ne\mu_{\rm e} + pe\mu_{\rm h} \tag{5}$$

$$R_{\rm H} = \frac{p\mu_{\rm h}^2 - n\mu_{\rm e}^2}{e(p\mu_{\rm h} + n\mu_{\rm e})^2}.$$
 (6)